

Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	4	kV
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ELECTRICAL CHARACTERISTICS (unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V R_L=33$	- -	MAX.	10	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM} T_j=125$ $R_L=3.3k$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	25	mA
				30	
I_H	$I_T=500mA$		MAX.	15	mA
dV/dt	$V_D=400V$ Gate Open $T_j=125$		MIN.	500	V/s
(dI/dt) _c	(dV/dt) _c =1.9 $V_j=125$		MIN.	3	A/ms
t_{on}	$I_G=20mA I_A=200mA I_R=20mA$ $T_j=25$		TYP.	2.5	s
t_{off}				25	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=17A t_p=380 \mu s$	$T_j=25$	1.5	V
V_{TO}	Threshold voltage	$T_j=125$	0.77	V
R_D	Dynamic resistance	$T_j=125$	35	Ω
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25$	5	A
I_{RRM}		$T_j=125$	0.4	

ORDERING INFORMATION

J ST 12 h3 Q (86)13.7 SWc -5.2

FIG.1: Maximum power dissipation versus RMS on-state current

FIG.2: RMS on-state current versus case temperature

PACKAGE MECHANICAL DATA



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